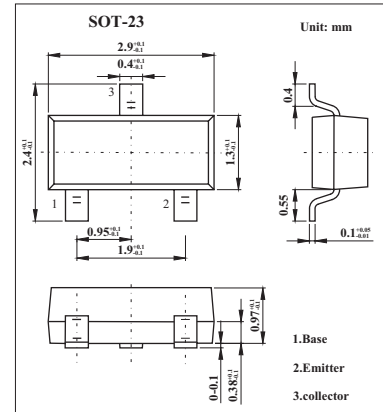




NPN Transistors

■ Features

- Excellent hFE linearity
- Collector Current : $I_c=0.5A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	40	V
Collector - Emitter Voltage	V_{CE0}	25	V
Emitter - Base Voltage	V_{EB0}	5	V
Collector Current - Continuous	I_c	500	mA
Collector Power Dissipation	P_c	300	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector - base breakdown voltage	V_{CB0}	$I_c = 100 \mu A, I_E = 0$	40			V
Collector - emitter breakdown voltage	V_{CE0}	$I_c = 0.1 mA, I_B = 0$	25			V
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu A, I_c = 0$	5			V
Collector cut - off current	I_{CBO}	$V_{CB} = 40 V, I_E = 0$			0.1	μA
Collector cut - off current	I_{CEO}	$V_{CE} = 20 V, I_B = 0$			0.1	μA
Emitter cut - off current	I_{EBO}	$V_{EB} = 5 V, I_c = 0$			0.1	μA
DC current gain	hFE	$V_{CE} = 1V, I_c = 50mA$	120		400	
		$V_{CE} = 1V, I_c = 500mA$	40			
Collector - emitter saturation voltage	$V_{CE(sat)}$	$I_c = 500 mA, I_B = 50mA$			0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 500 mA, I_B = 50mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 6V, I_c = 20mA, f = 30MHz$	150			MHz

■ hFE Classification

Marking	J3		
	L	H	J
hFE	120 to 200	200 to 350	300 to 400



■ Typical Characteristics

